









CEN2307B

-30V ▲ 50mΩ ▲ -3.7A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type
P-channel enhancement mode
UL94V-0 rated flame retardant epoxy
SOT23T package ▲ MSL 3
Super high dense cell density for extremely low R_{DS(ON)}

Rugged and reliable

MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-30V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	I _D	-3.7A
Pulsed Drain Current Note 1	I _{DM}	-14.8A
Maximum Power Dissipation	P _D	1.25W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

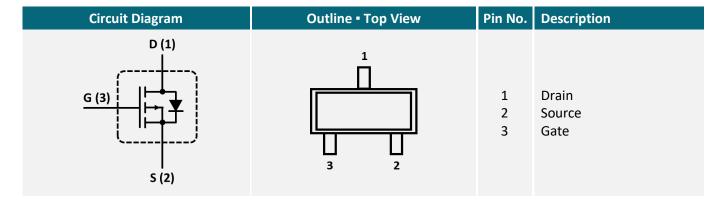
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	100°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB	ì
Converter	Fan	Switches	Banks	Storage	1
			4	¥	

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250 \mu A$	BV_{DSS}	-30			V
Zero Gate Voltage Drain Current	$V_{DS} = -30V$, $V_{GS} = 0V$	I _{DSS}			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I_{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\mu A$	$V_{GS(th)}$	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$, $I_D = -3.2A$	R _{DS(ON)}		50	60	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$, $I_D = -2.5A$	R _{DS(ON)}		63	82	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		550		pF
Output Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$ C_{OSS} 105					pF
Reverse Transfer Capacitance	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$ C_{RSS}					pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	$t_{\text{D(ON)}}$		10		ns
Turn-On Rise Time	V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	T _D		3		ns
Turn-Off Delay Time	V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	$t_{\text{D(OFF)}}$		33		ns
Turn-Off Fall Time	V_{DD} = -15V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t _F		4		ns
Total Gate Charge	V_{DS} = -15V, V_{GS} = -4.5V, I_D = -3.2A	\mathbf{Q}_{G}		6		nC
Gate Source Charge	$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -3.2A$	Q_{GS}		1		nC
Gate Drain Charge	$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_D = -3.2A$	Q_{GD}		3		nC
Drain-Source Diode Characteristics ar	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		I _S			-1	Α
Drain-Source Diode Forward Voltage Note3	$V_{GS} = 0V$, $I_S = -0.75A$	V_{SD}			-1.2	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Surface Mounted on FR4 Board, t ≤ 5 sec
- 3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

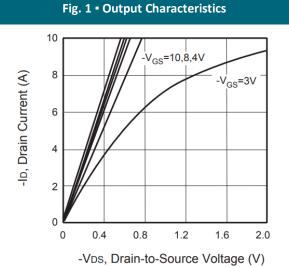


Fig. 2 • Transfer Characteristics

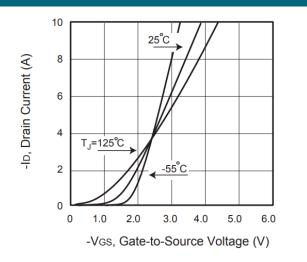


Fig. 3 • Capacitance

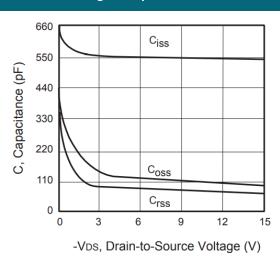


Fig. 4 • On-Resistance Variation with Temperature

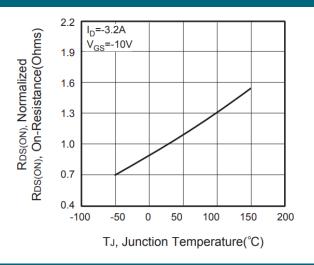


Fig. 5 • Gate Threshold Variation with Temperature

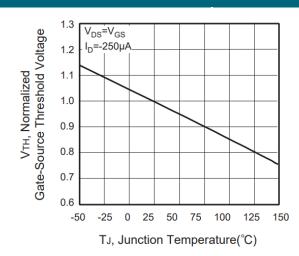
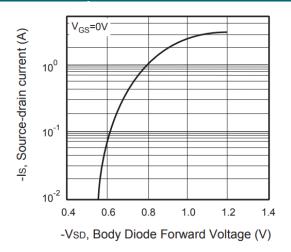


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 7 • Gate Charge

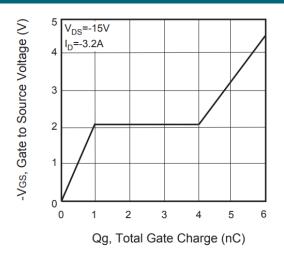


Fig. 8 • Maximum Safe Operating Area

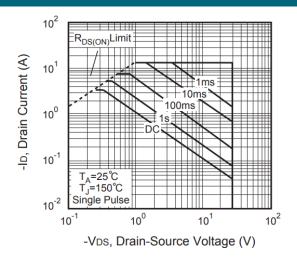
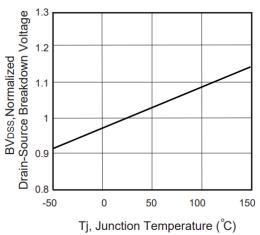


Fig. 9 • Breakdown Voltage Variation vs. Temperature





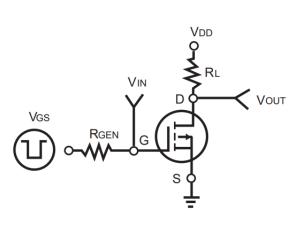
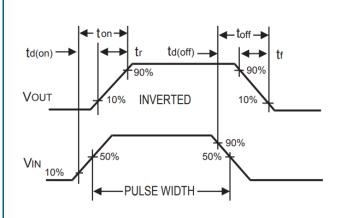


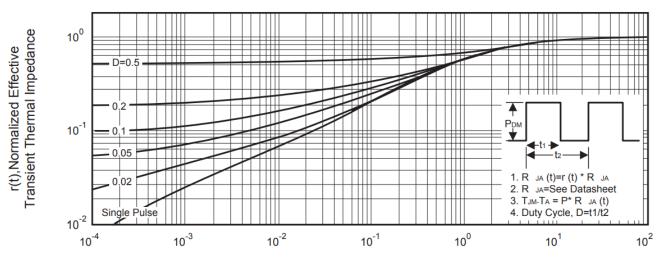
Fig. 11 • Switching Waveforms





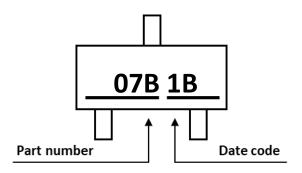
REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve



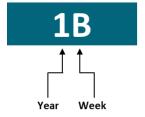
Square Wave Pulse Duration (sec)

PART MARKING

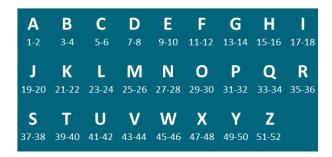


DATE CODE

Example: 1B



Coding list for "Week"

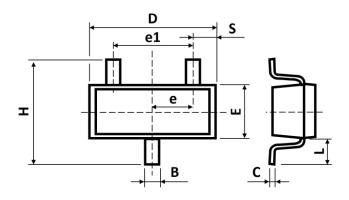


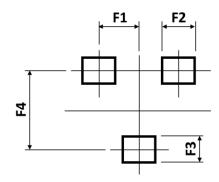
Coding list for "Year"





PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	0.950	-	1.100
A1	0.000	-	0.100
В	0.370	-	0.430
С	0.085	-	0.200
D	2.850	-	2.950
Е	1.250	-	1.350

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
е	0.900	-	1.000
e1	1.850	-	1.950
Н	2.350	-	2.450
L	0.500	-	0.600
S	0.410	-	0.610

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	0.950	-
F2	-	0.760	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F3	-	0.760	-
F4	-	2.290	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

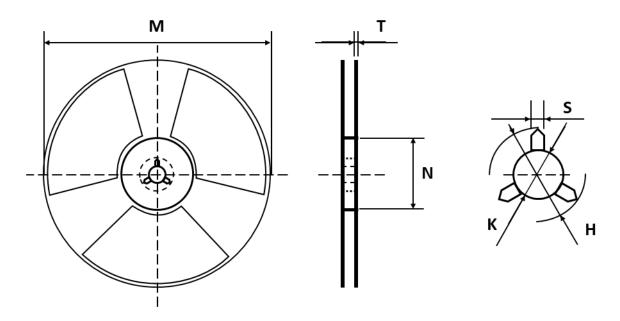
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.
CEN2307B	SOT23T	7" Reel	3,000pcs	15,000pcs

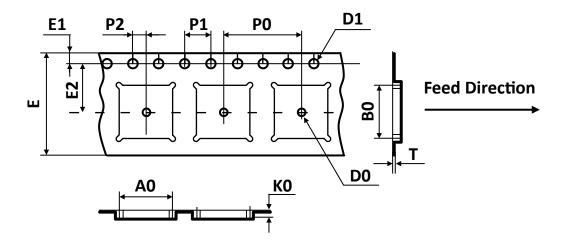


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	Т	Н	K	S
8mm	Ø180	Ø178.00	Ø54.00	1.20	20.00	13.30	3.00
OIIIII	ATOU	±1.00	±0.50	±0.20	±1.00	±0.30	±1.00

TAPE DIMENSIONS ▲ All dimensions in mm

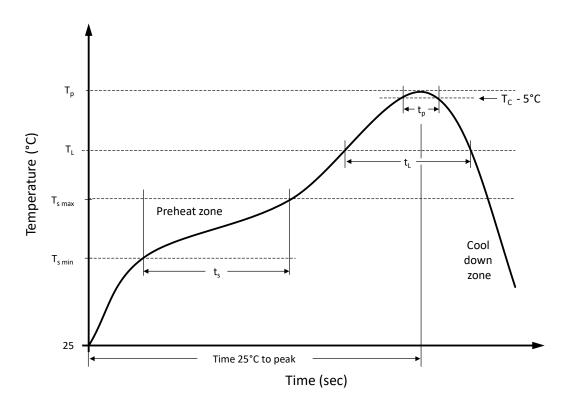


Package	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
SOT23T	3.25	2.80	1.22	1.00	1.50	8.00	1.75	3.50	4.00	4.00	2.00	0.20
301231	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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